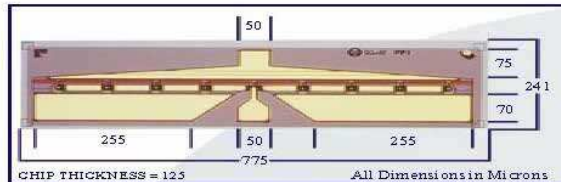


# MwT-1

## 12 GHz High Gain GaAs FET



DOWNLOAD ADDITIONAL DATA WWW.MWTINC.COM



### FEATURES

- 10 dB GAIN AT 12 GHz
- EXCELLENT FOR FEEDBACK AMPLIFIER APPLICATIONS 100 MHz TO 12 GHz
- 0.3 MICRON REFRACTORY METAL/GOLD GATE
- 630 MICRON GATE WIDTH
- CHOICE OF CHIP AND THREE PACKAGE TYPES

### DESCRIPTION

The MwT-1 is a GaAs MESFET device whose nominal quarter-micron gate length and 630 micron gate width make it ideally suited to applications requiring high-gain in the 100 MHz to 12 GHz frequency range. The straight geometry of the MwT-1 makes it equally effective for either wideband (e.g. 2 to 6 GHz) or narrow-band applications. The chip is produced using MwT's reliable metal system and devices from each wafer are screened to insure reliability. All chips are passivated using MwT's patented "Diamond-Like Carbon" process for increased durability. Designers can use MwT's unique BIN selection feature to choose devices from narrow Idss ranges, insuring consistent circuit operation.

### DC SPECIFICATIONS AT Ta = 25°C

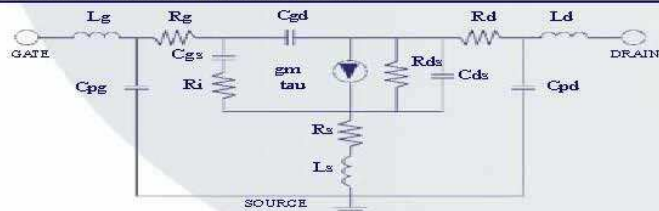
SYMBOL	PARAM. & CONDITIONS	UNITS	MIN	TYP	MAX
IDSS	Saturated Drain Current Vds= 4.0 V VGS= 0.0 V	mA	60		240
Gm	Transconductance Vds= 4.0 V VGS= 0.0 V	mS	90	120	
Vp	Pinch-off Voltage Vds= 3.0 V IDS= 4.0 mA	V		-2.0	-5.0
BVGSO	Gate-to-Source Breakdown Volt. Igs= -1.0 mA	V	-5.0	-10.0	
BVGDO	Gate-to-Drain Breakdown Volt. Igd= -1.0 mA	V	-6.0	-10.0	
Rth	Thermal Resistance MwT-1 Chip, 171 Resistance MwT-170, 173	°C/W		80	180*

\*Overall Rth depends on case in mounting.

### RF SPECIFICATIONS AT Ta = 25°C

SYMBOL	PARAMETERS AND CONDITIONS	FREQ	UNITS	MIN	TYP
P1dB	Output Power at 1 dB Compression VDS= 5.0 V IDS= 0.6 x IDSS	12 GHz	dBm	23.0	24.0
SSG	Small Signal Gain VDS= 5.0 V IDS= 0.6 x IDSS	12 GHz	dB	9.0	10.0
NFopt	Optimum Noise Figure VDS= 3.0 V IDS= 30 mA	12 GHz	dB		2.0
GA	Gain@Opt. NF VDS= 3.0 V IDS= 30 mA	12 GHz	dB		7.0
IDSS	Recommended IDSS Range for Optimum P1dB		mA		120-210

### DEVICE EQUIVALENT CIRCUIT MODEL



### PARAMETER

### VALUE

PARAMETER	VALUE
Source Resistance	R <sub>s</sub> 1.88 Ω
Source Inductance	L <sub>s</sub> 0.04 nH
Drain-Source Resistance	R <sub>ds</sub> 90 Ω
Drain-Source Capacitance	C <sub>ds</sub> 0.001 pF
Drain Resistance	R <sub>d</sub> 2.9 Ω
Drain Pad Capacitance	C <sub>pd</sub> 0.145 pF
Drain Inductance	L <sub>d</sub> 0.32 nH
Gate Bond Wire Inductance	L <sub>g</sub> 0.2 nH
Gate Pad Capacitance	C <sub>pg</sub> 0.09 pF
Gate Resistance	R <sub>g</sub> 0.83 Ω
Gate-Source Capacitance	C <sub>gs</sub> 0.64 pF
Channel Resistance	R <sub>i</sub> 4.11 Ω
Gate-Drain Capacitance	C <sub>gd</sub> 0.06 pF
Transconductance	gm 130.0 mS
Transit Time	tau 2.0 psec

### ORDERING INFORMATION

Chip	MwT-1
Package 70	MwT-170
Package 71	MwT-171
Package 73	MwT-173

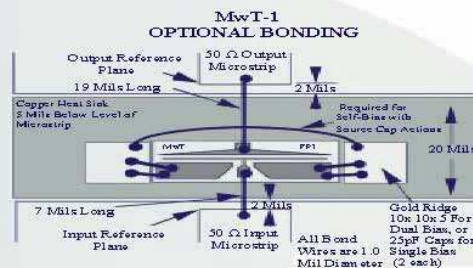
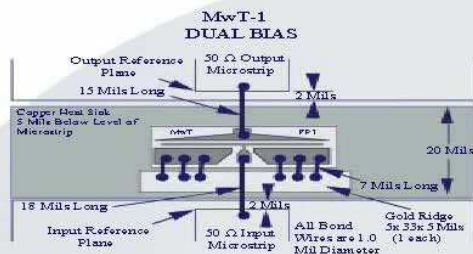
### NOTE:

For Package information, please see supplementary application note from our website at [www.mwtinc.com](http://www.mwtinc.com). When placing order or inquiring, please specify BIN range, wafer no., if known, and screening level required.

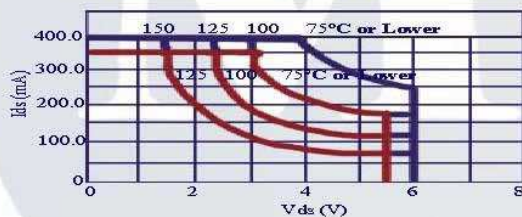
# MwT-1

## 12 GHz High Gain GaAs FET

### GaAs FET



SAFE OPERATING LIMITS vs. BACKSIDE CHIP



TYPICAL NOISE PARAMETERS

MwT-1LN Chip: VDS= 3.0V IDS= 30mA

FREQUENCY GHz	NF MIN dB	GAMMA OPT		Rn/50
		MAG	ANGLE	
1.00	0.45	0.885	32	1.27
2.00	0.63	0.722	61	0.5
4.00	0.95	0.591	110	0.24
6.00	1.25	0.61	139	0.17
8.00	1.52	0.656	157	0.14
12.00	1.88	0.733	176	0.11

Bin Selection Guide

Bin No.	A	B	C	D	E
Idss	60-	90-	120-	180-	210-
Range	90mA	120mA	180mA	210mA	240mA

#### BIN ACCURACY STATEMENT

When placing order or inquiring, please specify BIN range, wafer no., if known, and screening level required.

Absolute Maximum Continuous Maximum

#### MAXIMUM RATINGS AT Ta = 25°C

SYMBOL	PARAMETER	UNITS	CONT MAX	ABSOLUTE MAX
VDS	Drain to Source Voltage	V	See Safe Operating Limits	
Tch	Channel Temperature	°C	+150	+175
Tst	Storage Temperature	°C	-65 to +150	+175
Pin	RF Input Power	mW	200	300

NOTES: 1. Exceeding any one of these limits in continuous operation may reduce the mean time-to-failure below the design goals.  
2. Exceeding any one of these limits may cause permanent damage.

NOISE FIGURE AND ASSOCIATED GAIN VS. FREQUENCY

